

# Junhyeok Bang

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

38  
papers

878  
citations

17  
h-index

29  
g-index

40  
ext. papers

998  
ext. citations

6.8  
avg, IF

4.12  
L-index

#	Paper	IF	Citations
38	Substrate effect on hydrogen evolution reaction in two-dimensional MoC monolayers.. <i>Scientific Reports</i> , <b>2022</b> , 12, 6076	4.9	0
37	Fully Bottom-Up Waste-Free Growth of Ultrathin Silicon Wafer via Self-Releasing Seed Layer (Adv. Mater. 41/2021). <i>Advanced Materials</i> , <b>2021</b> , 33, 2170326	24	
36	Fully Bottom-Up Waste-Free Growth of Ultrathin Silicon Wafer via Self-Releasing Seed Layer. <i>Advanced Materials</i> , <b>2021</b> , 33, e2103708	24	3
35	Time-dependent density-functional theory molecular-dynamics study on amorphization of Sc-Sb-Te alloy under optical excitation. <i>Npj Computational Materials</i> , <b>2020</b> , 6,	10.9	14
34	Nonlocal effect of excited carriers on the bond strength of carbazole-based OLED host materials. <i>Physical Review Materials</i> , <b>2020</b> , 4,	3.2	3
33	Phase Transition in a Memristive Suspended MoS Monolayer Probed by Opto- and Electro-Mechanics. <i>ACS Nano</i> , <b>2020</b> , 14, 13611-13618	16.7	5
32	Carrier Dynamics and Transfer across the CdS/MoS Interface upon Optical Excitation. <i>Journal of Physical Chemistry Letters</i> , <b>2020</b> , 11, 6544-6550	6.4	7
31	Optical subpicosecond nonvolatile switching and electron-phonon coupling in ferroelectric materials. <i>Physical Review B</i> , <b>2020</b> , 102,	3.3	4
30	Photoinduced Vacancy Ordering and Phase Transition in MoTe. <i>Nano Letters</i> , <b>2019</b> , 19, 3612-3617	11.5	30
29	Dynamic defect as nonradiative recombination center in semiconductors. <i>Physical Review B</i> , <b>2019</b> , 100,	3.3	2
28	Directional Forces by Momentumless Excitation and Order-to-Order Transition in Peierls-Distorted Solids: The Case of GeTe. <i>Physical Review Letters</i> , <b>2018</b> , 120, 185701	7.4	21
27	Doping-induced antiferromagnetic bicollinear insulating state and superconducting temperature of monolayer FeSe systems. <i>Physical Review B</i> , <b>2018</b> , 98,	3.3	2
26	Strain-induced indium clustering in non-polar a-plane InGaN quantum wells. <i>Acta Materialia</i> , <b>2018</b> , 145, 109-122	8.4	5
25	Robust ferromagnetism in hydrogenated graphene mediated by spin-polarized pseudospin. <i>Scientific Reports</i> , <b>2018</b> , 8, 13940	4.9	4
24	Giant lattice expansion by quantum stress and universal atomic forces in semiconductors under instant ultrafast laser excitation. <i>Physical Chemistry Chemical Physics</i> , <b>2017</b> , 19, 24735-24741	3.6	5
23	Phonon-Enabled Carrier Transport of Localized States at Non-Polar Semiconductor Surfaces: A First-Principles-Based Prediction. <i>Journal of Physical Chemistry Letters</i> , <b>2016</b> , 7, 3548-53	6.4	5
22	Carrier-Multiplication-Induced Structural Change during Ultrafast Carrier Relaxation and Nonthermal Phase Transition in Semiconductors. <i>Physical Review Letters</i> , <b>2016</b> , 117, 126402	7.4	20

21	The role of collective motion in the ultrafast charge transfer in van der Waals heterostructures. <i>Nature Communications</i> , <b>2016</b> , 7, 11504	17.4	79
20	Triangular Black Phosphorus Atomic Layers by Liquid Exfoliation. <i>Scientific Reports</i> , <b>2016</b> , 6, 23736	4.9	24
19	Carrier-induced transient defect mechanism for non-radiative recombination in InGaN light-emitting devices. <i>Scientific Reports</i> , <b>2016</b> , 6, 24404	4.9	9
18	Multivalency-Induced Band Gap Opening at MoS2 Edges. <i>Chemistry of Materials</i> , <b>2015</b> , 27, 3326-3331	9.6	39
17	Molecular doping of ZnO by ammonia: a possible shallow acceptor. <i>Journal of Materials Chemistry C</i> , <b>2015</b> , 3, 339-344	7.1	24
16	Microscopic Origin for Electrically Benign Small-angle Grain Boundaries in Low-cost Semiconductors. <i>Materials Research Letters</i> , <b>2014</b> , 2, 51-56	7.4	3
15	Understanding the presence of vacancy clusters in ZnO from a kinetic perspective. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 252101	3.4	33
14	Difficulty in predicting shallow defects with hybrid functionals: Implication of the long-range exchange interaction. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	15
13	Electron-rich driven electrochemical solid-state amorphization in Li-Si alloys. <i>Nano Letters</i> , <b>2013</b> , 13, 4511-4515	4.5	45
12	Regulating energy transfer of excited carriers and the case for excitation-induced hydrogen dissociation on hydrogenated graphene. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , <b>2013</b> , 110, 908-11	11.5	29
11	Deep electron traps and origin of p-type conductivity in the earth-abundant solar-cell material Cu <sub>2</sub> ZnSnS <sub>4</sub> . <i>Physical Review B</i> , <b>2013</b> , 87,	3.3	97
10	Atomic and electronic structures of single-layer FeSe on SrTiO <sub>3</sub> (001): The role of oxygen deficiency. <i>Physical Review B</i> , <b>2013</b> , 87,	3.3	76
9	Suppression of nonradiative recombination in ionic insulators by defects: Role of fast electron trapping in Tl-doped CsI. <i>Physical Review B</i> , <b>2013</b> , 87,	3.3	11
8	Ab initio study of boron segregation and deactivation at Si/SiO <sub>2</sub> interface. <i>Microelectronic Engineering</i> , <b>2012</b> , 89, 120-123	2.5	14
7	Modification of Defect Structures in Graphene by Electron Irradiation: Ab Initio Molecular Dynamics Simulations. <i>Journal of Physical Chemistry C</i> , <b>2012</b> , 116, 16070-16079	3.8	55
6	Phase diagram of graphene nanoribbons and band-gap bifurcation of Dirac fermions under quantum confinement. <i>Physical Review B</i> , <b>2012</b> , 85,	3.3	15
5	Electronic Structure of O-vacancy in High-k Dielectrics and Oxide Semiconductors. <i>Materials Research Society Symposia Proceedings</i> , <b>2011</b> , 1370, 3		
4	Electronic structure and transport properties of hydrogenated graphene and graphene nanoribbons. <i>New Journal of Physics</i> , <b>2010</b> , 12, 125005	2.9	17

- 3 Localization and one-parameter scaling in hydrogenated graphene. *Physical Review B*, **2010**, 81, 33 41
- 2 Atomic Structure and Diffusion of Hydrogen in ZnO. *Journal of the Korean Physical Society*, **2009**, 55, 98-102 0.6 18
- 1 Diffusion and thermal stability of hydrogen in ZnO. *Applied Physics Letters*, **2008**, 92, 132109 3.4 104